2M x 8-Bit Dynamic RAM
2k-Refresh

HYB 3117800BSJ(L)-50/-60/-70

Advanced Information

- 2 097 152 words by 8-bit organization
- 0 to 70 °C operating temperature
- Performance:

		-50	-60	-70	
t_{RAC}	$\overline{RAS}$ access time	50	60	70	ns
t_{CAC}	$\overline{CAS}$ access time	13	15	20	ns
t_{AA}	Access time from address	25	30	35	ns
t_{RC}	Read/Write cycle time	90	110	130	ns
t_{PC}	Fast page mode cycle time	35	40	45	ns

- Single + 3.3 V (0.3 V) supply
- Low power dissipation
  max. 432 active mW (-50 version)
  max. 396 active mW (-60 version)
  max. 360 active mW (-70 version)
  7.2 mW standby (LV-TTL)
  3.6 mW standby (CMOS)
  720 µW standby for L-version
- Output unlatched at cycle end allows two-dimensional chip selection
- Read, write, read-modify-write, $\overline{CAS}$-before-$\overline{RAS}$ refresh, $\overline{RAS}$-only refresh, hidden refresh,self refresh and test mode
- Fast page mode capability
- All inputs, outputs and clocks fully LVTTL-compatible
- 2048 refresh cycles / 32 ms
- Plastic Package: P-SOJ-28-3 400 mil

The HYB 3117800BSJ is a 16 MBit dynamic RAM organized as 2097152 words by 8-bits. The HYB 3117800BSJ utilizes a submicron CMOS silicon gate process technology, as well as advanced circuit techniques to provide wide operating margins, both internally and for the system user. Multiplexed address inputs permit the HYB 3117800BSJ to be packaged in a standard SOJ-28 400 mil plastic package. These packages provide high system bit densities and are compatible with commonly used automatic testing and insertion equipment. System-oriented features include single + 3.3 V (0.3 V) power supply, direct interfacing with high-performance logic device families. The HYB 3117800BSJL parts have a very low power „sleep mode" supported by Self Refresh.

Ordering Information

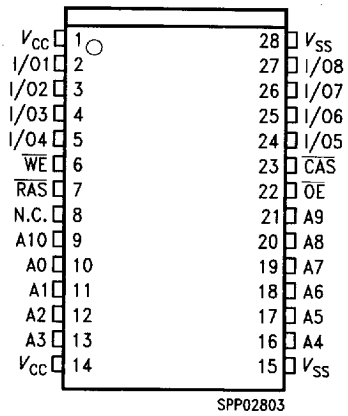
Type	Ordering Code	Package	Descriptions
HYB 3117800BSJ-50	on request	P-SOJ-28-3 400 mil	3.3V DRAM (access time 50 ns)
HYB 3117800BSJ-60	on request	P-SOJ-28-3 400 mil	3.3V DRAM (access time 60 ns)
HYB 3117800BSJ-70	on request	P-SOJ-28-3 400 mil	3.3V DRAM (access time 70 ns)
HYB 3117800BSJL-50	on request	P-SOJ-28-3 400 mil	3.3V LP-DRAM (access time 50 ns)
HYB 3117800BSJL-60	on request	P-SOJ-28-3 400 mil	3.3V LP-DRAM (access time 60 ns)
HYB 3117800BSJL-70	on request	P-SOJ-28-3 400 mil	3.3V LP-DRAM (access time 70 ns)

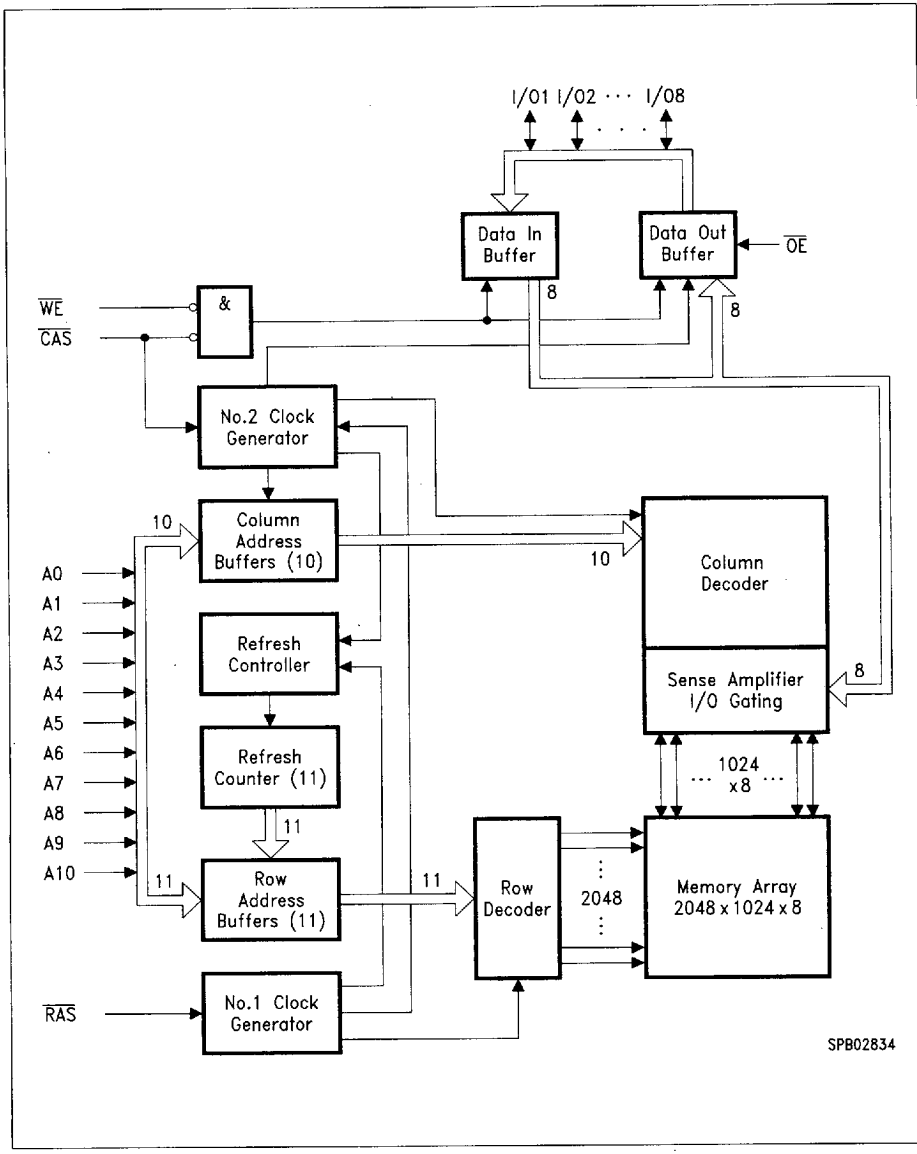
Pin Names

A0 to A10	Row Address Inputs
A0 to A9	Column Address Inputs
RAS	Row Address Strobe
OE	Output Enable
I/O1-I/O8	Data Input/Output
CAS	Column Address Strobe
WE	Read/Write Input
V_{CC}	Power Supply (+ 3.3 V)
V_{SS}	Ground (0 V)
N.C.	Not connected

Pin Configuration
(top view)

P-SOJ-28-3 (400mil)





Block Diagram

Absolute Maximum Ratings

Operating temperature range ..... 0 to 70 °C

Storage temperature range ..... – 55 to 150 °C

Input/output voltage ..... – 0.5 to min (V_{CC} + 0.5, 4.6) V

Power supply voltage ..... – 1.0 V to 4.6 V

Power dissipation ..... 0.5 W

Data out current (short circuit) ..... 50 mA

Note: *Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage of the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

DC Characteristics

T_A = 0 to 70 °C, V_{SS} = 0 V, V_{CC} = 3.3 V ± 0.3 V, t_T = 5 ns

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Input high voltage	V_{IH}	2.0	V_{CC} + 0.5	V	1)
Input low voltage	V_{IL}	– 0.5	0.8	V	1)
LVTTL Output high voltage (I_{OUT} = – 2 mA)	V_{OH}	2.4	–	V	1)
LVTTL Output low voltage (I_{OUT} = 2 mA)	V_{OL}	–	0.4	V	1)
CMOS Output high voltage (I_{OUT} = – 100 mA)	V_{OH}	V_{CC} – 0.2	–	V	
CMOS Output low voltage (I_{OUT} = 100 mA)	V_{OL}	–	0.2	V	
Input leakage current,any input ($0 V \le V_{IH} \le V_{CC}$ + 0.3 V, all other pins = 0 V)	$I_{I(L)}$	– 10	10	μA	1)
Output leakage current (DO is disabled, $0 V \le V_{OUT} \le V_{CC}$ + 0.3 V)	$I_{O(L)}$	– 10	10	μA	1)
Average V_{CC} supply current:	I_{CC1}				2) 3) 4)
-50 ns version		–	120	mA	2) 3) 4)
-60 ns version		–	110	mA	2) 3) 4)
-70 ns version		–	100	mA	
($\overline{RAS}$, $\overline{CAS}$, address cycling, t_{RC} = t_{RC} min.)					
Standby V_{CC} supply current ($\overline{RAS}$ = $\overline{CAS}$ = V_{IH})	I_{CC2}	–	2	mA	–
Average V_{CC} supply current, during $\overline{RAS}$-only refresh cycles:	I_{CC3}				2) 4)
-50 ns version		–	120	mA	2) 4)
-60 ns version		–	110	mA	2) 4)
-70 ns version		–	100	mA	
($\overline{RAS}$ cycling: $\overline{CAS}$ = V_{IH}, t_{RC} = t_{RC} min.)					

DC Characteristics (cont'd)
T_A = 0 to 70 °C, V_{SS} = 0 V, V_{CC} = 3.3 V ± 0.3 V, t_T = 5 ns

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Average V_{CC} supply current, during fast page mode: -50 ns version	I_{CC4}	–	40	mA	2) 3) 4)
-60 ns version		–	35	mA	2) 3) 4)
-70 ns version		–	30	mA	2) 3) 4)
($\overline{RAS}$ = V_{IL}, $\overline{CAS}$, address cycling, t_{PC} = t_{PC} min.)					
Standby V_{CC} supply current	I_{CC5}	–	1	mA	1)
($\overline{RAS}$ = $\overline{CAS}$ = V_{CC} – 0.2 V)			200	µA	L-version
Average V_{CC} supply current, during $\overline{CAS}$-before-RAS refresh mode: -50 ns version	I_{CC6}	–	120	mA	2) 4)
-60 ns version		–	110	mA	2) 4)
-70 ns version		–	100	mA	2) 4)
($\overline{RAS}$, $\overline{CAS}$ cycling, t_{RC} = t_{RC} min.)					
Average Self Refresh Current ($\overline{CBR}$ cycle with t_{RAS} > t_{RASS} min., $\overline{CAS}$ held low, $\overline{WE}$ = V_{CC} – 0.2 V, Address and Din = V_{CC} – 0.2 V or 0.2 V)	I_{CC7}	–	1	mA	
			250	µA	L-version

Capacitance
T_A = 0 to 70 °C, V_{CC} = 3.3 V ± 0.3 V, f = 1 MHz

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Input capacitance (A0 to A10)	C_{I1}	–	5	pF
Input capacitance ($\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$)	C_{I2}	–	7	pF
I/O capacitance (I/O1-I/O8)	C_{IO}	–	7	pF

AC Characteristics [5)6)]

16F

T_A = 0 to 70 °C, V_{CC} = 3.3 V 0.3 V, t_T = 5 ns

Parameter	Symbol	Limit Values						Unit	Note
		-50		-60		-70			
		min.	max.	min.	max.	min.	max.		
Common Parameters									
Random read or write cycle time	t_{RC}	90	–	110	–	130	–	ns	
$\overline{RAS}$ precharge time	t_{RP}	30	–	40	–	50	–	ns	
$\overline{RAS}$ pulse width	t_{RAS}	50	10k	60	10k	70	10k	ns	
$\overline{CAS}$ pulse width	t_{CAS}	13	10k	15	10k	20	10k	ns	
Row address setup time	t_{ASR}	0	–	0	–	0	–	ns	
Row address hold time	t_{RAH}	8	–	10	–	10	–	ns	
Column address setup time	t_{ASC}	0	–	0	–	0	–	ns	
Column address hold time	t_{CAH}	10	–	15	–	15	–	ns	
$\overline{RAS}$ to $\overline{CAS}$ delay time	t_{RCD}	18	37	20	45	20	50		
$\overline{RAS}$ to column address delay time	t_{RAD}	13	25	15	30	15	35	ns	
$\overline{RAS}$ hold time	t_{RSH}	13		15	–	20	–	ns	
$\overline{CAS}$ hold time	t_{CSH}	50		60	–	70	–	ns	
$\overline{CAS}$ to $\overline{RAS}$ precharge time	t_{CRP}	5	–	5	–	5	–	ns	
Transition time (rise and fall)	t_T	3	50	3	50	3	50	ns	7
Refresh period	t_{REF}	–	32	–	32	–	32	ms	
Refresh period for L-version	t_{REF}	–	256	–	256	–	256	ms	
Read Cycle									
Access time from $\overline{RAS}$	t_{RAC}	–	50	–	60	–	70	ns	8, 9
Access time from $\overline{CAS}$	t_{CAC}	–	13	–	15	–	20	ns	8, 9
Access time from column address	t_{AA}	–	25	–	30	–	35	ns	8,10
$\overline{OE}$ access time	t_{OEA}	–	13	–	15	–	20	ns	
Column address to $\overline{RAS}$ lead time	t_{RAL}	25	–	30	–	35	–	ns	
Read command setup time	t_{RCS}	0	–	0	–	0	–	ns	
Read command hold time	t_{RCH}	0	–	0	–	0	–	ns	11
Read command hold time referenced to $\overline{RAS}$	t_{RRH}	0	–	0	–	0	–	ns	11
$\overline{CAS}$ to output in low-Z	t_{CLZ}	0	–	0	–	0	–	ns	8

AC Characteristics (cont'd) [5][6] 16F

T_A = 0 to 70 °C, V_{CC} = 3.3 V 0.3 V, t_T = 5 ns

Parameter	Symbol	Limit Values						Unit	Note
		-50		-60		-70			
		min.	max.	min.	max.	min.	max.		
Output buffer turn-off delay	t_{OFF}	0	13	0	15	0	20	ns	12
Output buffer turn-off delay from $\overline{OE}$	t_{OEZ}	0	13	0	15	0	20	ns	12
Data to $\overline{OE}$ low delay	t_{DZO}	0	–	0	–	0	–	ns	13
$\overline{CAS}$ high to data delay	t_{CDD}	13	–	15	–	20	–	ns	14
$\overline{OE}$ high to data delay	t_{ODD}	13	–	15	–	20	–	ns	14
Write Cycle									
Write command hold time	t_{WCH}	8	–	10	–	10	–	ns	
Write command pulse width	t_{WP}	8	–	10	–	10	–	ns	
Write command setup time	t_{WCS}	0	–	0	–	0	–	ns	15
Write command to $\overline{RAS}$ lead time	t_{RWL}	13	–	15	–	20	–	ns	
Write command to $\overline{CAS}$ lead time	t_{CWL}	13	–	15	–	20	–	ns	
Data setup time	t_{DS}	0	–	0	–	0	–	ns	16
Data hold time	t_{DH}	10	–	10	–	15	–	ns	16
Data to $\overline{CAS}$ low delay	t_{DZC}	0	–	0	–	0	–	ns	13
Read-Modify-Write Cycle									
Read-write cycle time	t_{RWC}	126	–	150	–	180	–	ns	
$\overline{RAS}$ to $\overline{WE}$ delay time	t_{RWD}	68	–	80	–	95	–	ns	15
$\overline{CAS}$ to $\overline{WE}$ delay time	t_{CWD}	31	–	35	–	45	–	ns	15
Column address to $\overline{WE}$ delay time	t_{AWD}	43	–	50	–	60	–	ns	15
$\overline{OE}$ command hold time	t_{OEH}	13	–	15	–	20	–	ns	
Fast Page Mode Cycle									
Fast page mode cycle time	t_{PC}	35	–	40	–	45	–	ns	
$\overline{CAS}$ precharge time	t_{CP}	10	–	10	–	10	–	ns	
Access time from $\overline{CAS}$ precharge	t_{CPA}	–	30	–	35	–	40	ns	7
$\overline{RAS}$ pulse width	t_{RAS}	50	200k	60	200k	70	200k	ns	
$\overline{CAS}$ precharge to $\overline{RAS}$ Delay	t_{RHPC}	30	–	35	–	40	–	ns	

AC Characteristics (cont'd) [5)6)] 16F

T_A = 0 to 70 °C, V_{CC} = 3.3 V 0.3 V, t_T = 5 ns

Parameter	Symbol	Limit Values						Unit	Note
		-50		-60		-70			
		min.	max.	min.	max.	min.	max.		
Fast Page Mode Read-Modify-Write Cycle									
Fast page mode read-write cycle time	t_{PRWC}	71	–	80	–	95	–	ns	
$\overline{CAS}$ precharge to $\overline{WE}$	t_{CPWD}	48	–	55	–	65	–	ns	
$\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle									
$\overline{CAS}$ setup time	t_{CSR}	10	–	10	–	10	–	ns	
$\overline{CAS}$ hold time	t_{CHR}	10	–	10	–	10	–	ns	
$\overline{RAS}$ to $\overline{CAS}$ precharge time	t_{RPC}	5	–	5	–	5	–	ns	
Write to $\overline{RAS}$ precharge time	t_{WRP}	10	–	10	–	10	–	ns	
Write hold time referenced to $\overline{RAS}$	t_{WRH}	10	–	10	–	10	–	ns	
$\overline{CAS}$-before-$\overline{RAS}$ Counter Test Cycle									
$\overline{CAS}$ precharge time	t_{CPT}	35	–	40	–	40	–	ns	
Test Mode									
$\overline{CAS}$ hold time	t_{CHRT}	30	–	30	–	30	–	ns	
Write command setup time	t_{WTS}	10	–	10	–	10	–	ns	
Write command hold time	t_{WTH}	10	–	10	–	10	–	ns	
Self Refresh Cycle									
$\overline{RAS}$ pulse width	t_{RASS}	100k	–	100k	–	100k	–	ns	17
$\overline{RAS}$ precharge time	t_{RPS}	95	–	110	–	130	–	ns	17
$\overline{CAS}$ hold time	t_{CHS}	– 50	–	– 50	–	– 50	–	ns	17

Notes:

1) All voltages are referenced to V_{SS}.

2) I_{CC1}, I_{CC3}, I_{CC4} and I_{CC6} depend on cycle rate.

3) I_{CC1} and I_{CC4} depend on output loading. Specified values are measured with the output open.

4) Address can be changed once or less while $\overline{RAS} = V_{IL}$. In the case of I_{CC4} it can be changed once or less during a fast page mode cycle (t_{PC}).

5) An initial pause of 200 ms is required after power-up followed by 8 RAS cycles of which at least one cycle has to be a refresh cycle, before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 CAS-before-RAS initialization cycles instead of 8 RAS cycles are required.

6) AC measurements assume t_T = 5 ns.

7) $V_{IH\ (min.)}$ and $V_{IL\ (max.)}$ are reference levels for measuring timing of input signals. Transition times are also measured between V_{IH} and V_{IL}.

8) Measured with a load equivalent to 100 pF and at V_{OH} = 2.0 V (I_{OH} = – 2mA) , V_{OH} = 0.8 V (I_{OL} = 2 mA).

9) Operation within the $t_{RCD\ (max.)}$ limit ensures that $t_{RAC\ (max.)}$ can be met. $t_{RCD\ (max.)}$ is specified as a reference point only: If t_{RCD} is greater than the specified $t_{RCD\ (max.)}$ limit, then access time is controlled by t_{CAC}.

10) Operation within the $t_{RAD\ (max.)}$ limit ensures that $t_{RAC\ (max.)}$ can be met. $t_{RAD\ (max.)}$ is specified as a reference point only: If t_{RAD} is greater than the specified $t_{RAD\ (max.)}$ limit, then access time is controlled by t_{AA}.

11) Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.

12) $t_{OFF\ (max.)}$ and $t_{OEZ\ (max.)}$ define the time at which the outputs achieve the open-circuit condition and are not referenced to output voltage levels.

13) Either t_{DZC} or t_{DZO} must be satisfied.

14) Either t_{CDD} or t_{ODD} must be satisfied.

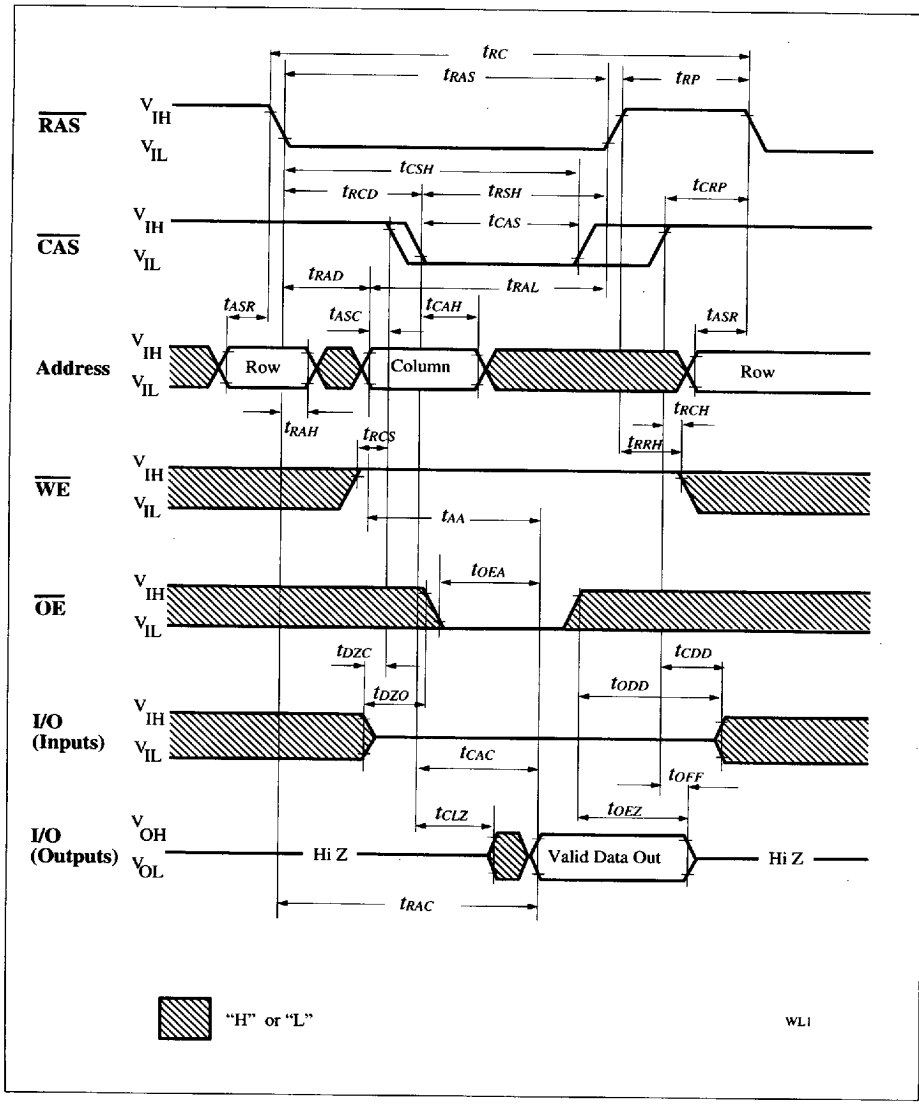
15) t_{WCS}, t_{RWD}, t_{CWD}, t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} > t_{WCS\ (min.)}$, the cycle is an early write cycle and the I/O pin will remain open-circuit (high impedance) through the entire cycle; if $t_{RWD} > t_{RWD\ (min.)}$, $t_{CWD} > t_{CWD\ (min.)}$, $t_{AWD} > t_{AWD\ (min.)}$ and $t_{CPWD} > t_{CPWD\ (min.)}$, the cycle is a read-write cycle and I/O pins will contain data read from the selected cells. If neither of the above sets of conditions is satisfied, the condition of the I/O pins (at access time) is indeterminate.

16) These parameters are referenced to the CAS leading edge in early write cycles and to the WE leading edge in read-write cycles.

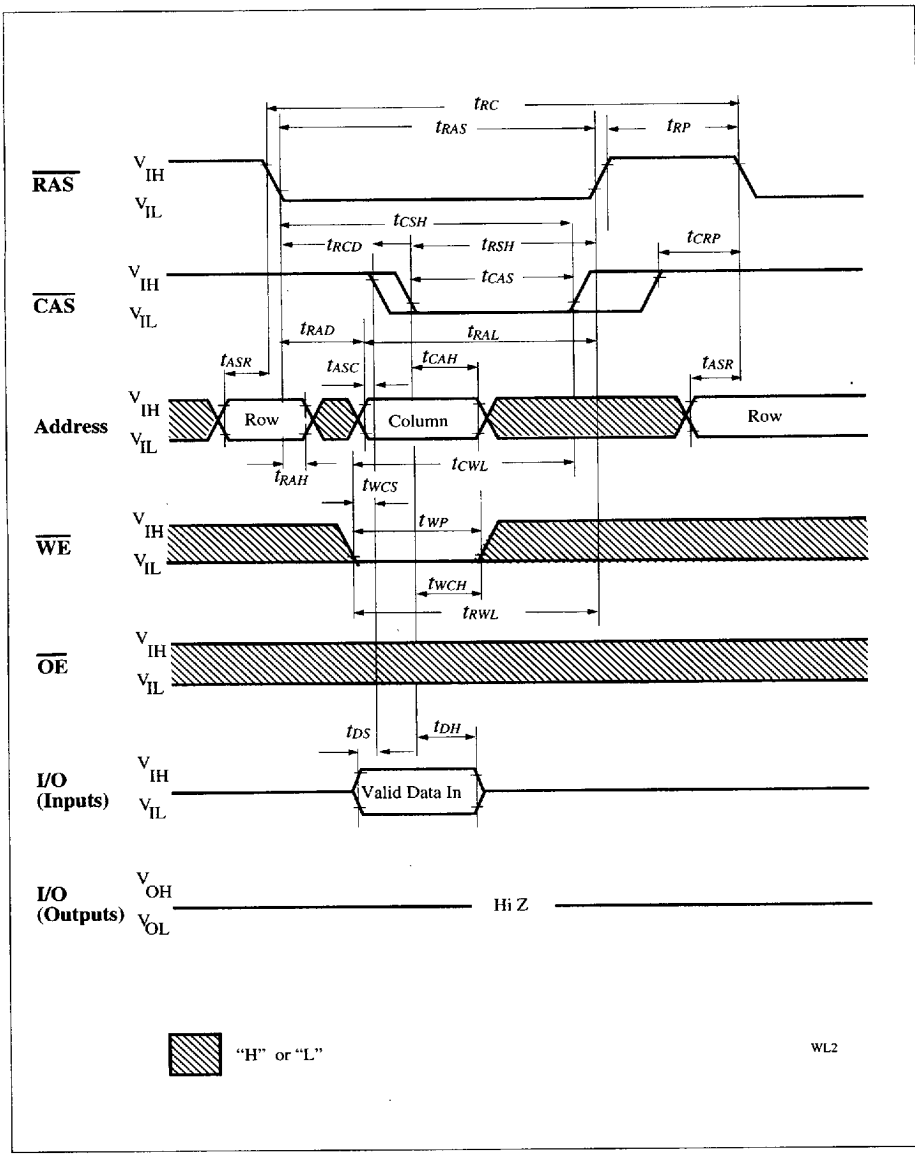
17) When using Self Refresh mode, the following refresh operations must be performed to ensure proper DRAM operation:

If row addresses are being refreshed on an evenly distributed manner over the refresh interval using CBR refresh cycles, then only one CBR cycle must be performed immediately after exit from Self Refresh.

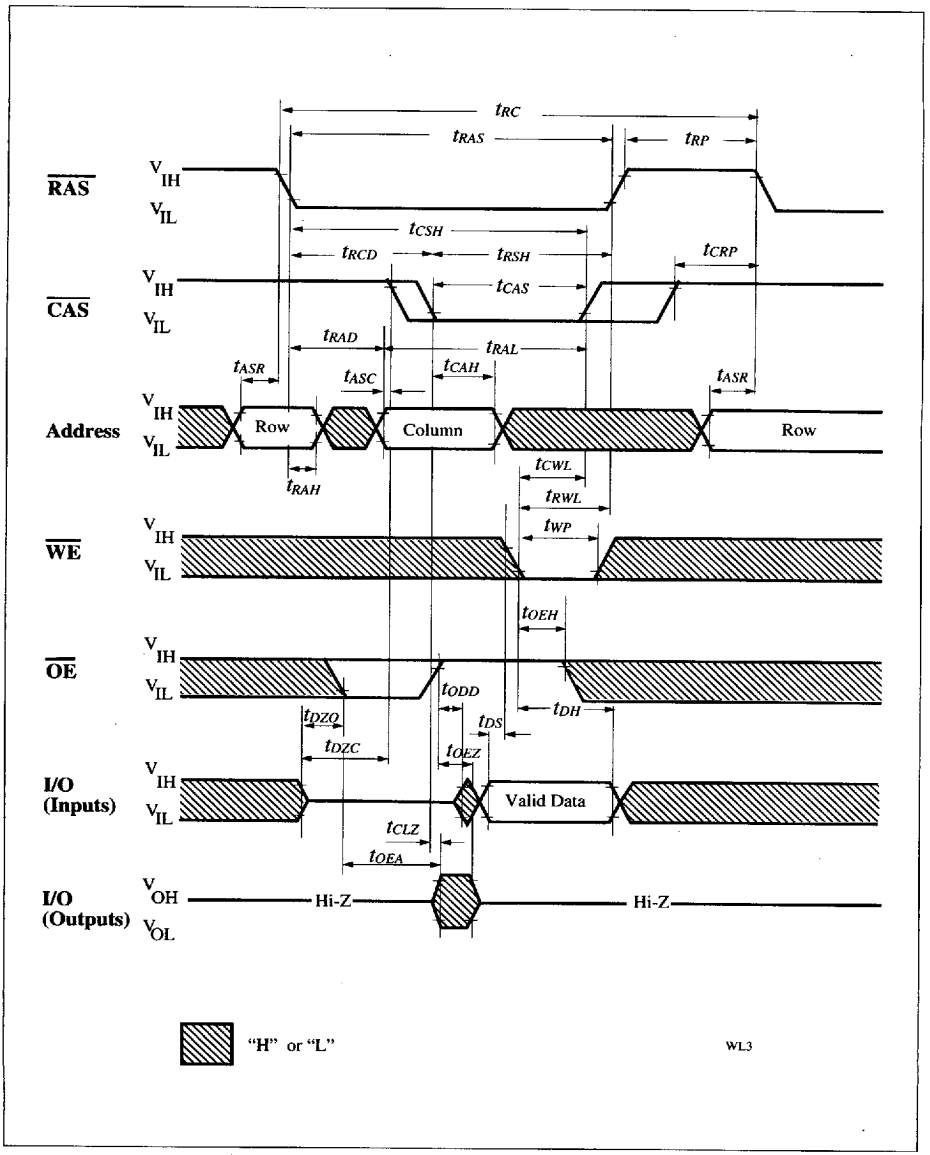
If row addresses are being refreshed in any other manner (ROR - Distributed/Burst; or CBR-Burst) over the refresh interval, then a full set of row refreshes must be performed immediately before entry to and immediately after exit from Self Refresh.



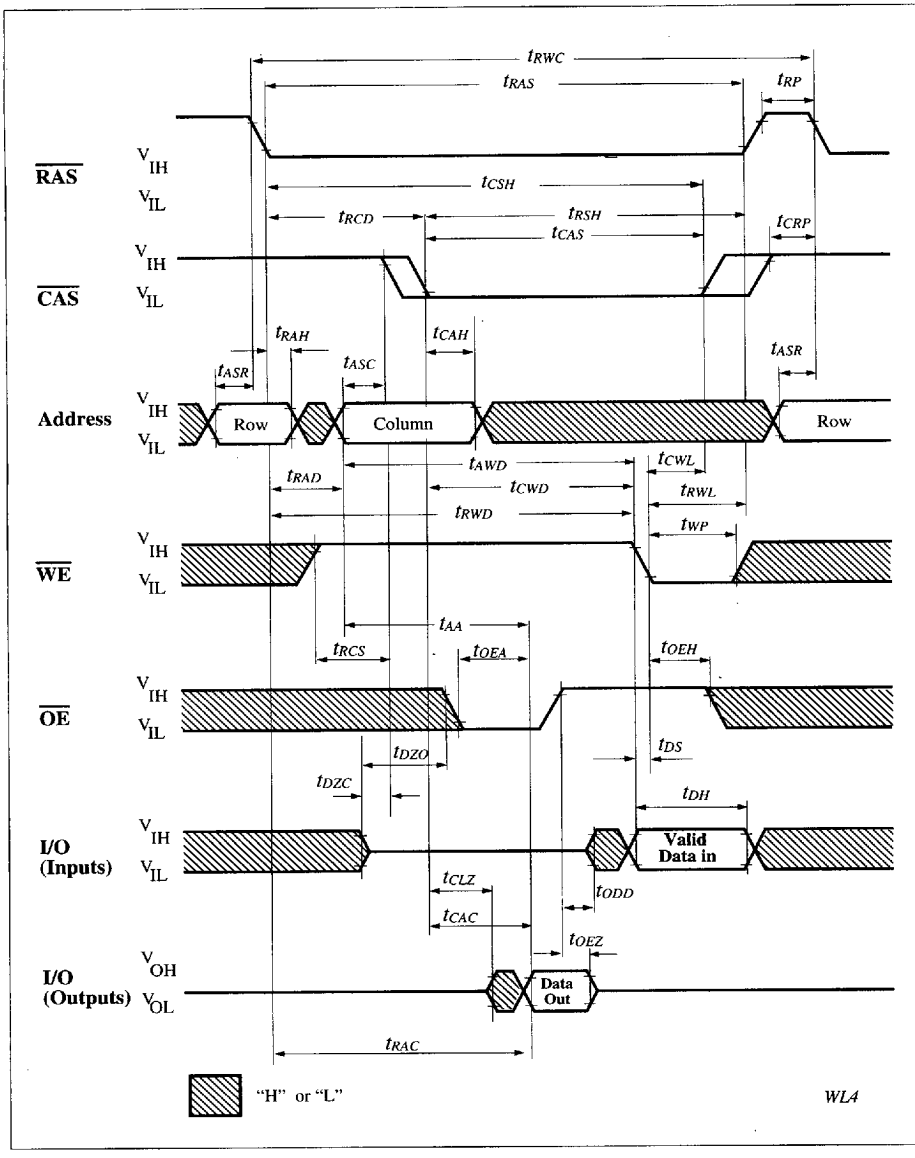
Read Cycle



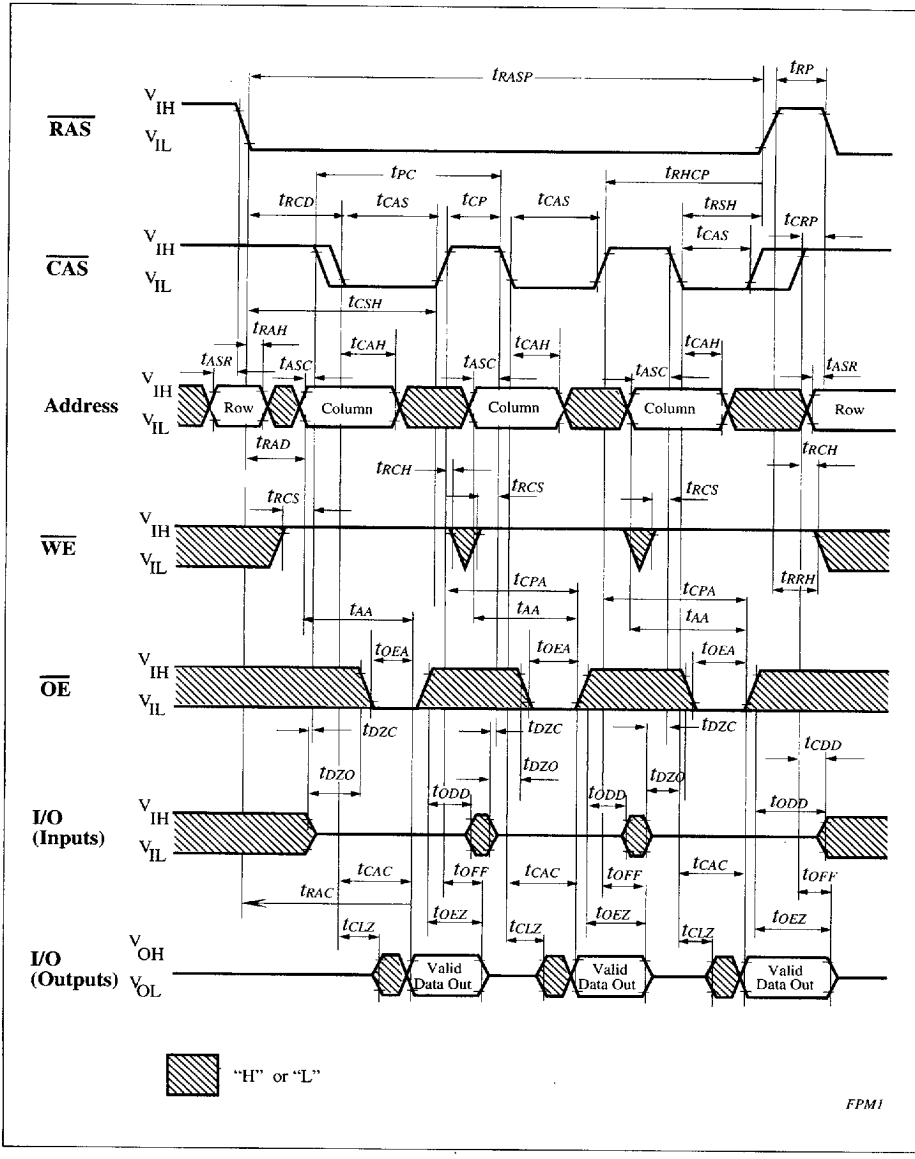
Write Cycle (Early Write)



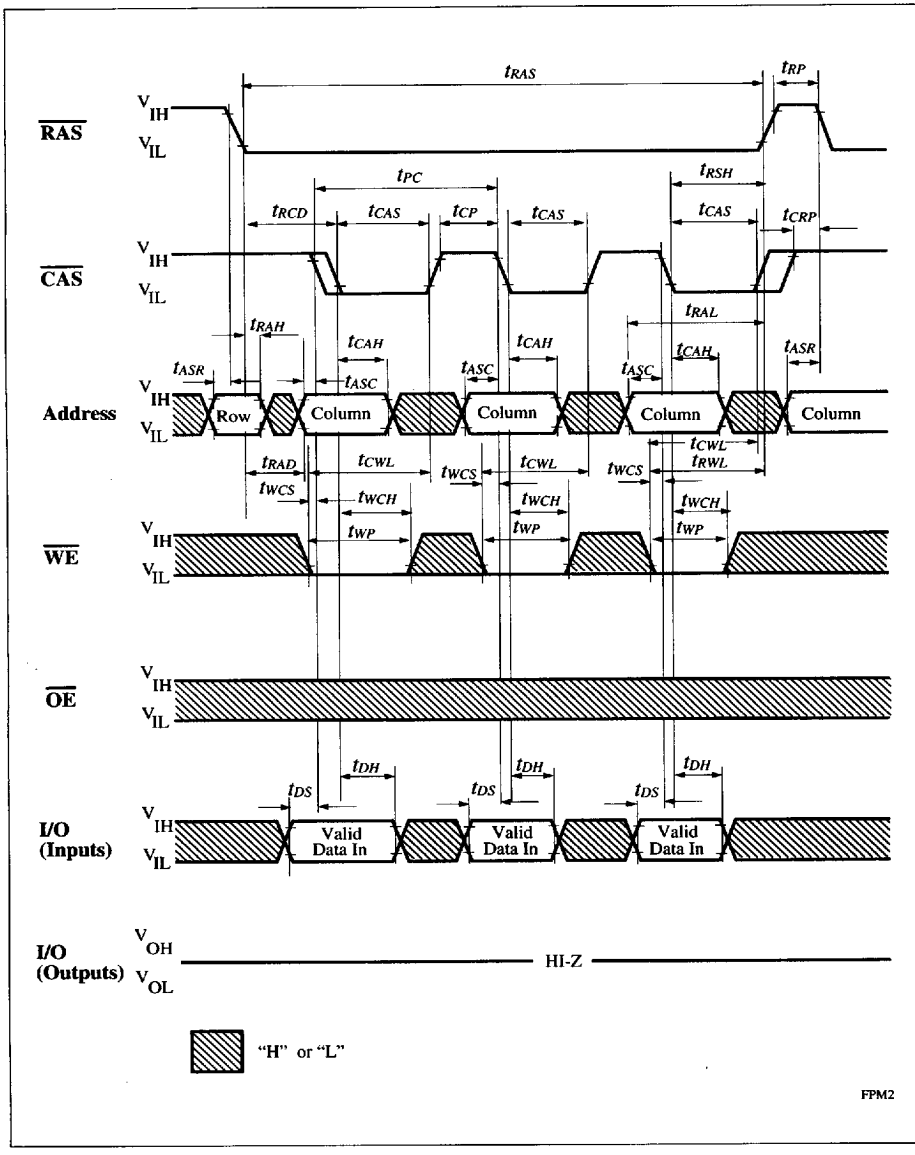
Write Cycle ($\overline{OE}$ Controlled Write)



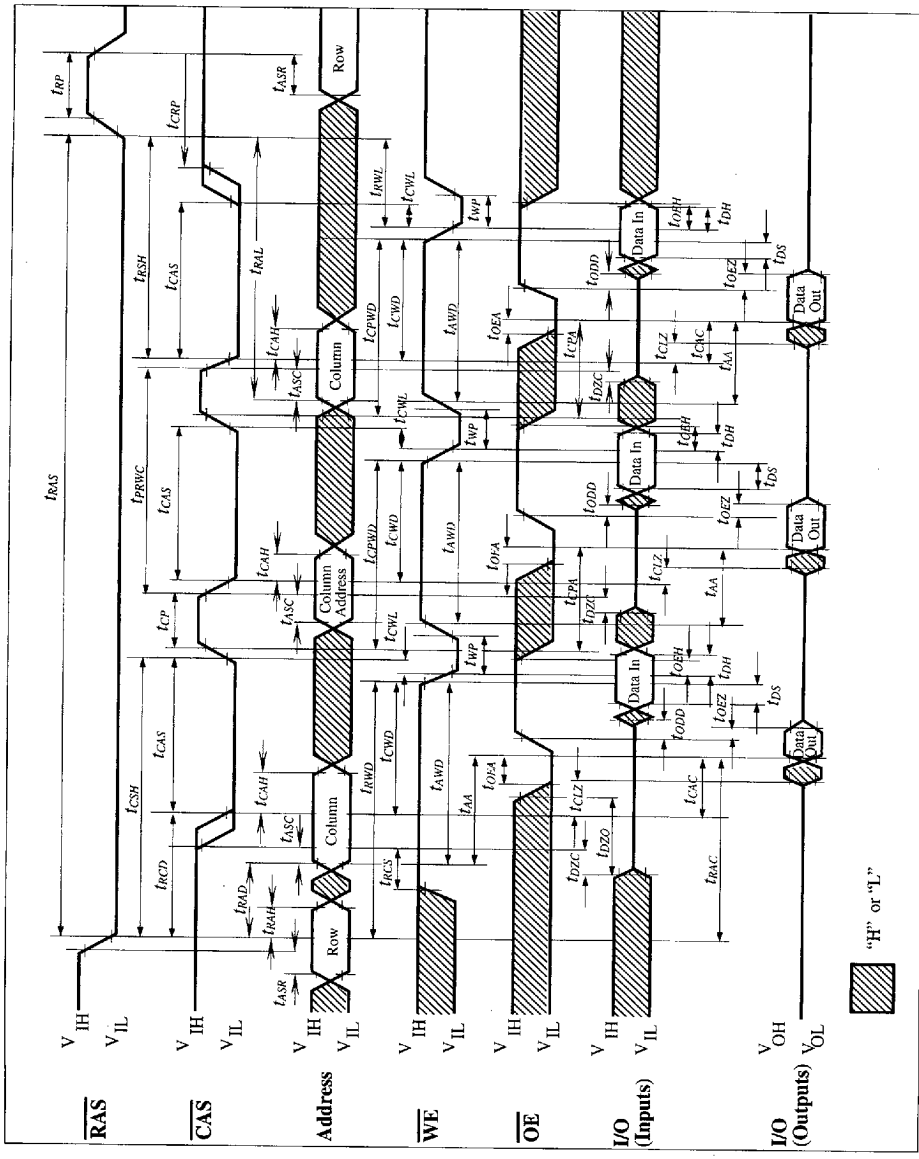
Read-Write (Read-Modify-Write) Cycle



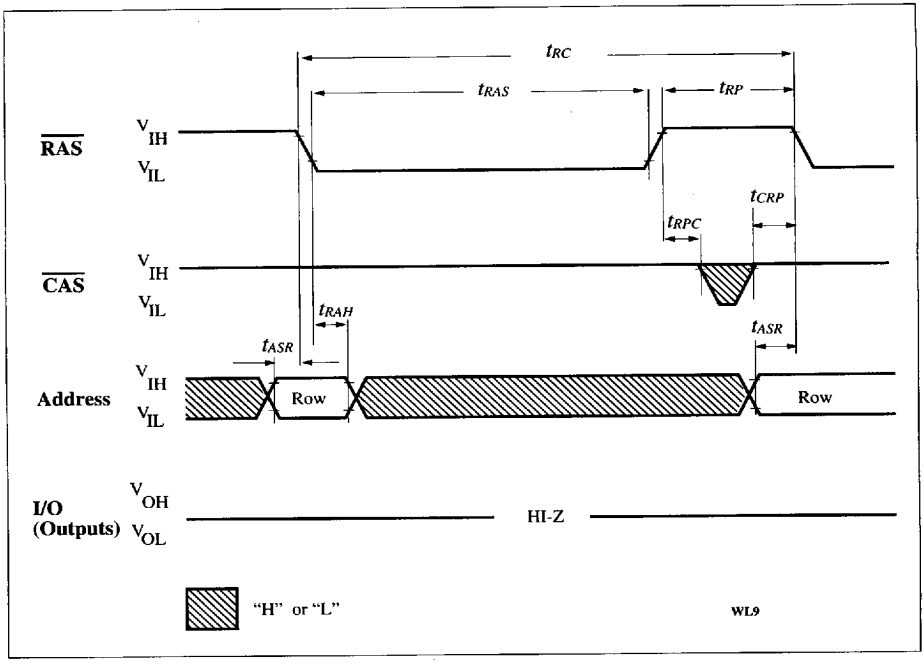
Fast Page Mode Read Cycle



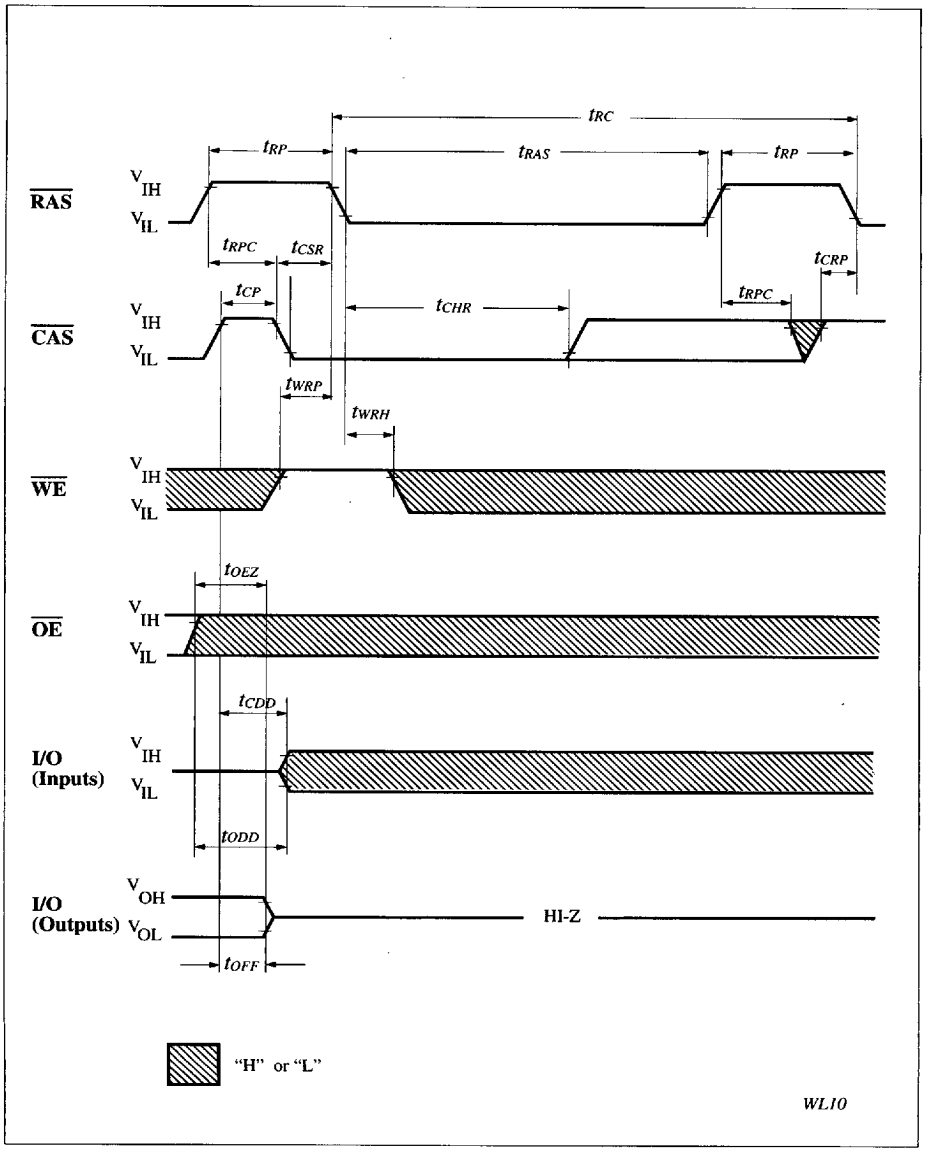
Fast Page Mode Early Write Cycle



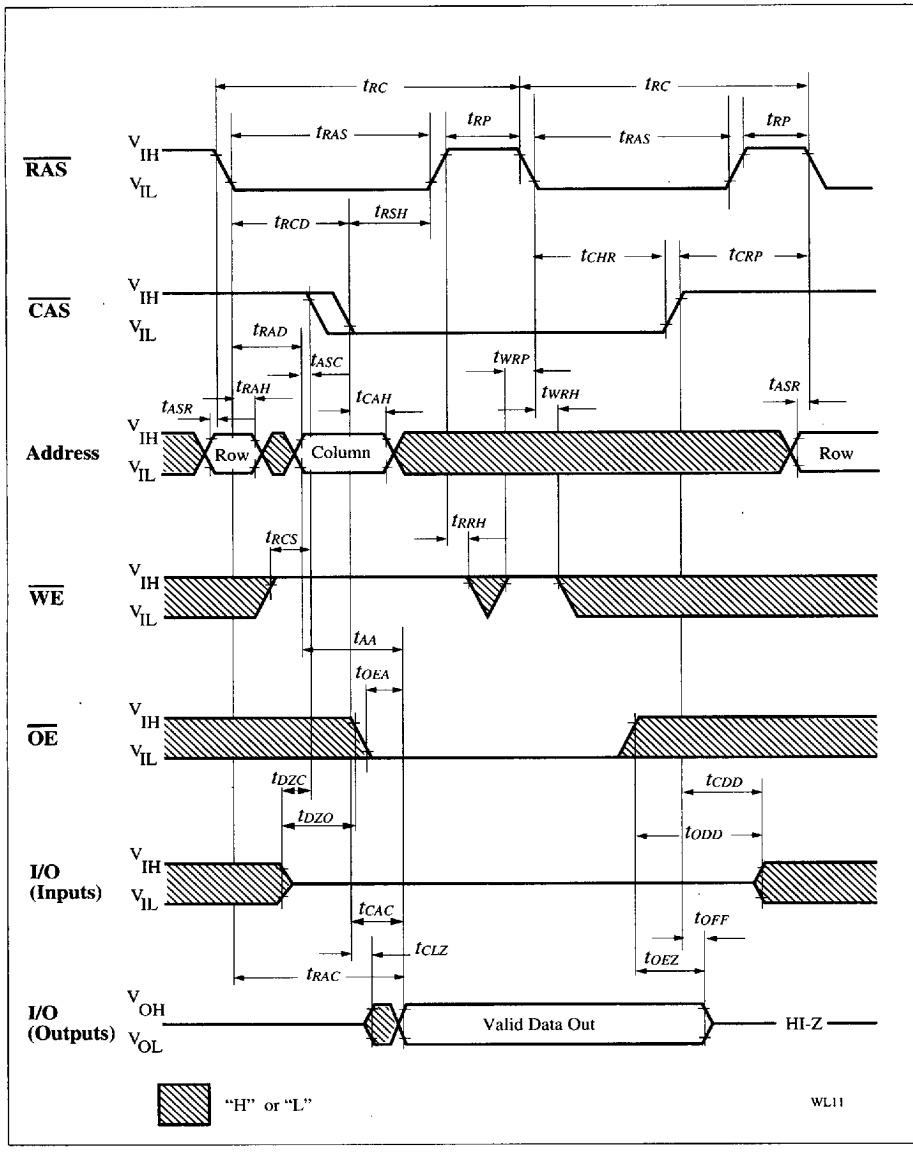
Fast Page Mode Read-Modify-Write Cycle



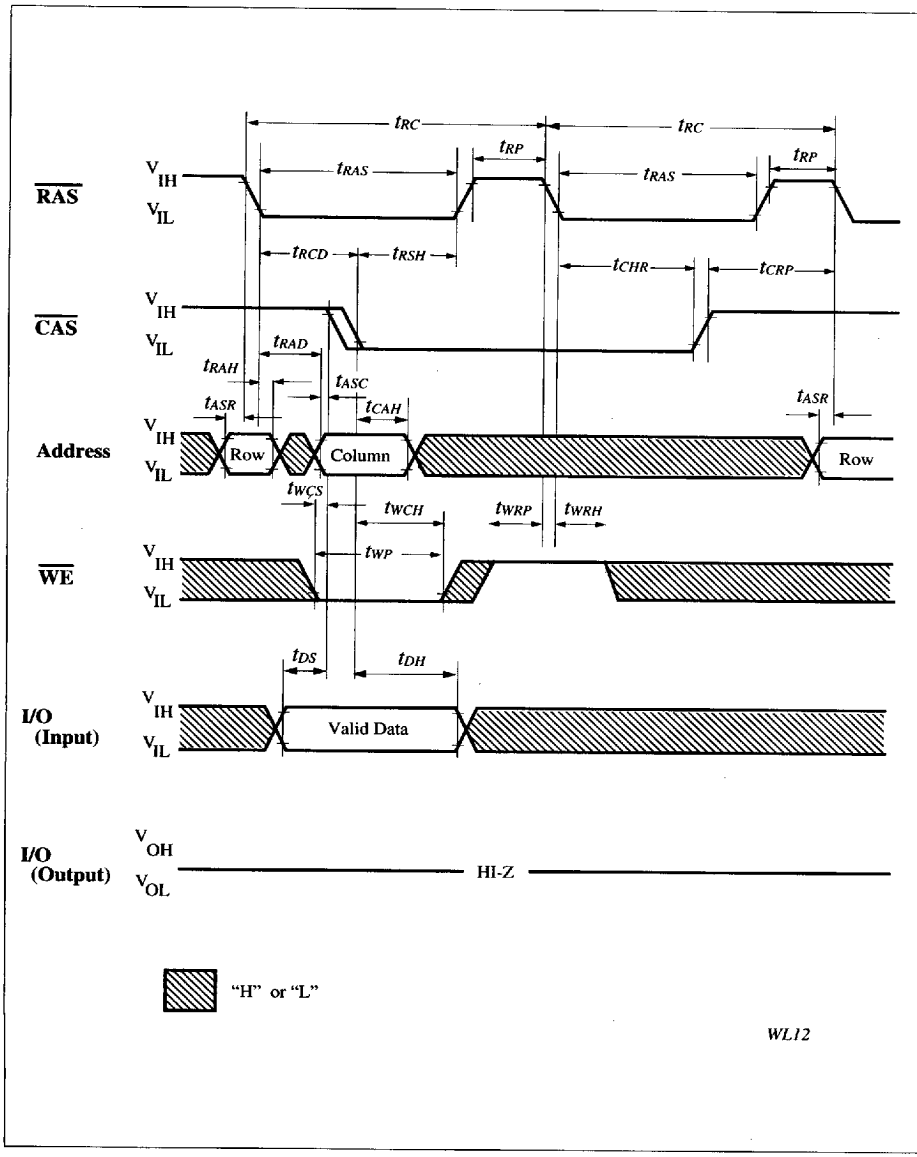
RAS-Only Refresh Cycle



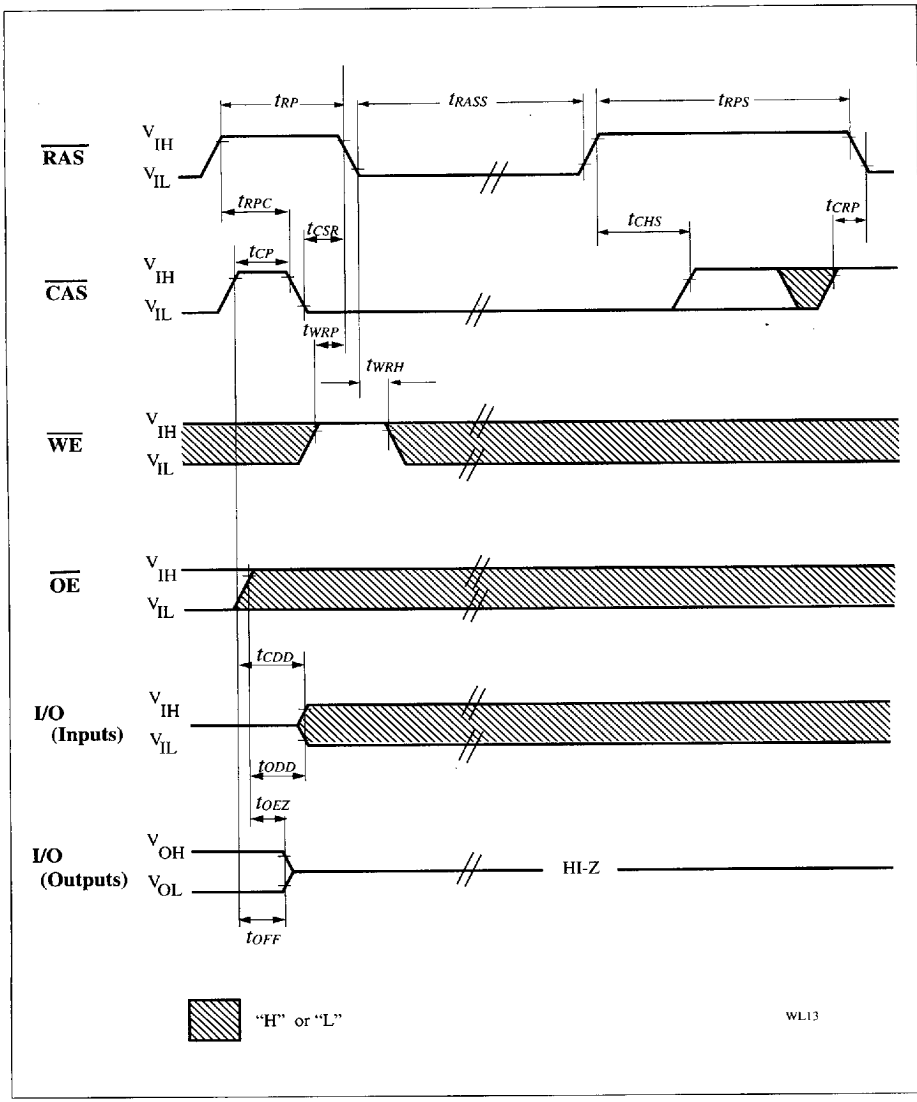
CAS-Before-RAS Refresh Cycle



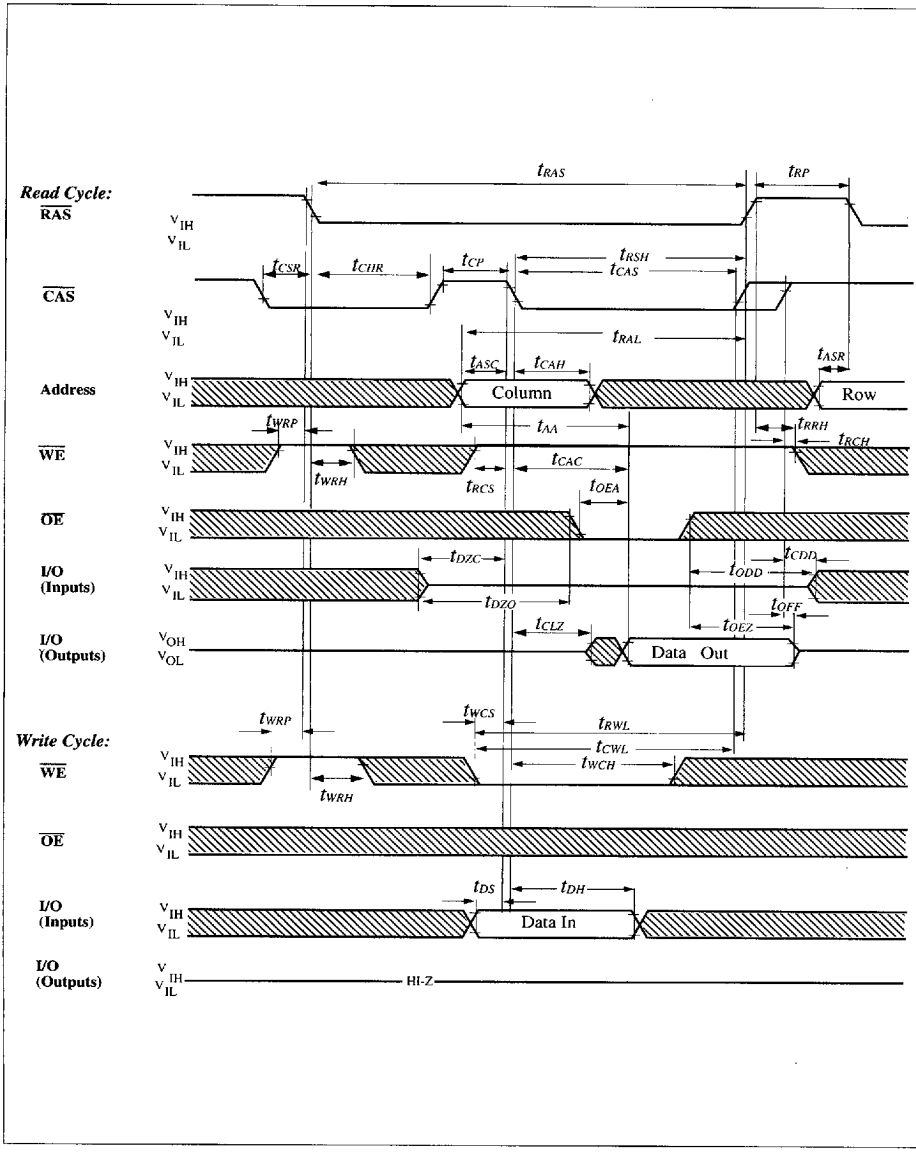
Hidden Refresh Cycle (Read) Cycle



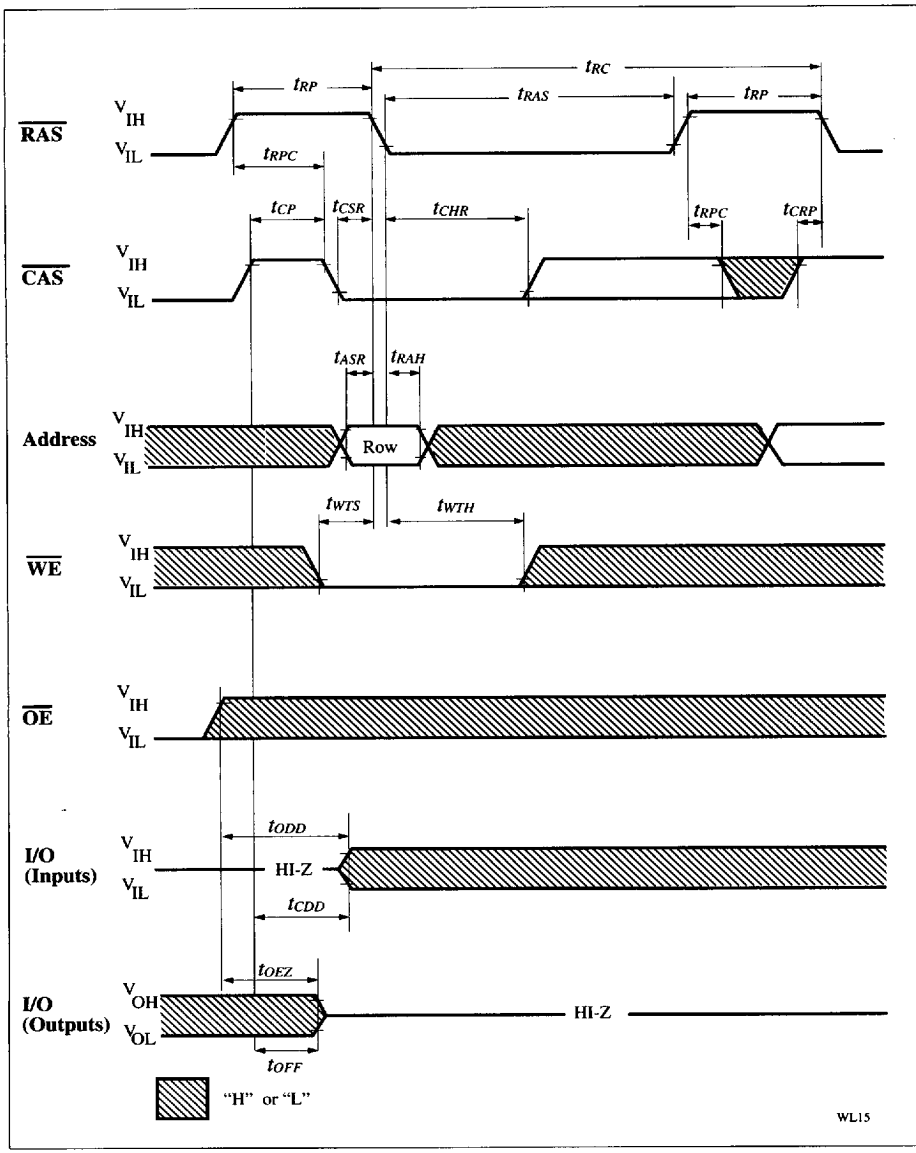
Hidden Refresh Cycle (Early Write)



CAS before RAS Self Refresh Cycle



CAS-Before-RAS Refresh Counter Test Cycle



Test Mode Entry

Test Mode

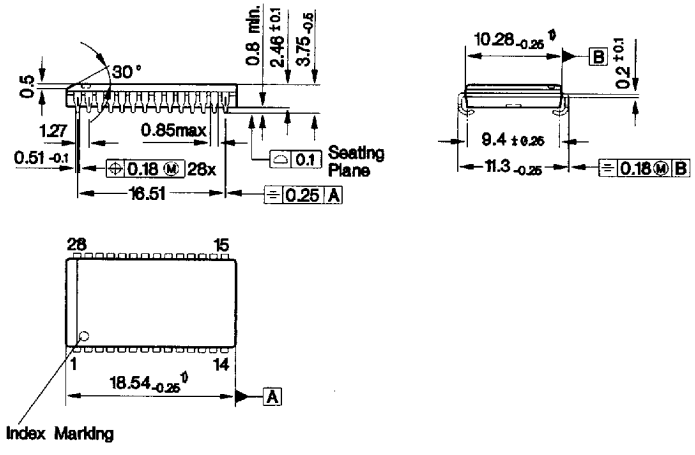
As the HYB 3117800BSJ is organized internally as 1M x 16-bits, a test mode cycle using 2:1 compression can be used to improve test time. Note that in the 2M x 8 version the test time is reduced by 1/2 for a N test pattern.

In a test mode "write" the data from each I/O pin is written into two 1M blocks simultaneously (all "1" s or all "0" s). In test mode "read" each I/O output is used for indicating the test mode result. If the internal two bits are equal, the I/O would indicate a "1". If they were not equal, the I/O would indicate a "0". The WCBR cycle ($\overline{WE}$, $\overline{CAS}$ before $\overline{RAS}$) puts the device into test mode. To exit from test mode, a "$\overline{CAS}$ before $\overline{RAS}$ refresh", "$\overline{RAS}$ only refresh" or "Hidden refresh" can be used. Refresh during test mode operation can be performed by normal read cycles or by WCBR refresh cylces.

Row addresses A0 through A9 have to kept high to perform a testmode entry cycle. All other addresses are don't care.

Package Outlines

P-SOJ-28-3 (400 mil)
(Small Outline J-leaded Package)



1) Does not include plastic or metal protrusion of 0.15 max. per side

GPJ05699

Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".
SMD = Surface Mounted Device

Dimensions in mm